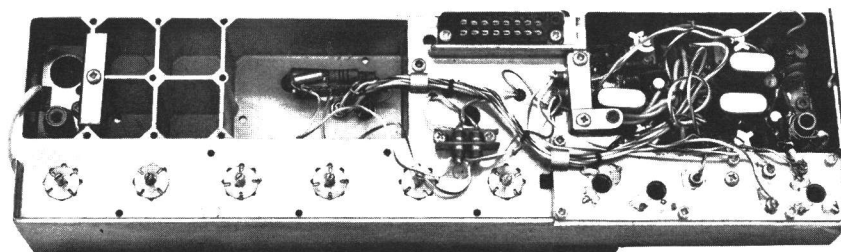


MASTR[®] PROGRESS LINE

150.8—174 MHz DUAL FRONT END MODEL 19D413462-G1



SPECIFICATIONS *

FREQUENCY RANGE	150.8-174 MHz		
SENSITIVITY (DFE & RECEIVER)	With Pre-Amp	Without Pre-Amp	With Noise Blanker
12-dB SINAD	0.35 μ v	0.60 μ v	0.35 μ v
20-dB quieting	0.45 μ v	0.85 μ v	0.45 μ v
INTERMODULATION (EIA)	-75 dB	-80 dB	-75 dB
INPUT POWER	.010 Amps at 10 volts		
FREQUENCY STABILITY			
Standard Oscillator	.0005% (-30°C to +60°C)		
ICOM	.0002% (-30°C to +60°C)		
TRANSISTORS	6		
DIMENSIONS (HxWxD)	2-1/4" x 11-3/4" x 4-3/8"		

OPTIONS

7351: 1-Freq. Standard	7356: 3-Freq. with Pre-Amp
7352: 2-Freq. Standard	7357: 1-Freq. with ICOM Osc.
7353: 3-Freq. Standard	7358: 2-Freq. with ICOM Osc.
7354: 1-Freq. with Pre-Amp	7359: 3-Freq. with ICOM Osc.
7355: 2-Freq. with Pre-Amp	

*These specifications are intended primarily for the use of the serviceman. Refer to the appropriate Specification Sheet for the complete specifications.

TABLE OF CONTENTS

SPECIFICATIONS	Cover
DESCRIPTION	1
Dual Front End	1
Antenna System	1
CIRCUIT ANALYSIS	2
Dual Front End	2
RF Pre-Amplifier	2
Helical Resonators	2
Standard Oscillator/Multiplier	2
Oscillator/Multiplier with ICOM	3
2nd Multiplier	3
1st Mixer	3
Hi IF Amplifier	3
RECEIVER MODIFICATIONS	4
MAINTENANCE	4
Disassembly	4
Frequency Change	5
Test Procedures	8
ICOM Adjustment	8
Alignment Procedure	9
OUTLINE DIAGRAM	10
SCHEMATIC DIAGRAMS	
DFE with Standard Oscillator	11
DFE with ICOM	13
PARTS LIST	12
PRODUCTION CHANGES	14
ILLUSTRATIONS	
Figure 1 - Dual Front End Block Diagram	1
Figure 2 - Single Antenna Block Diagram	2
Figure 3 - Frequency Combinations	3
Figure 4 - FET Nomenclature	4
Figure 5 - Typical Diode Assembly Connection	4
Figure 6 - Dual Front End Disassembly	5

WARNING

No one should be permitted to handle any portion of the equipment that is supplied with voltage or RF power; or to connect any external apparatus to the units while the units are supplied with power. KEEP AWAY FROM LIVE CIRCUITS.

DESCRIPTION

DUAL FRONT END

General Electric Dual Front End Model 19D413462G1 operates in the 150.8-174 megahertz band. The Dual Front End (DFE) is used with MASTR Progress Line Receivers to monitor up to four frequencies when the channel spacing is greater than 0.4% ($\pm 0.2\%$). The standard DFE can be used with standard receivers or with 25-50 MHz receivers for cross-band application. The DFE with Pre-Amp can be used with 150.8-174 MHz receivers with Noise Blankers or receivers with Pre-Amp.

The DFE is of single-unit construction, completely housed in an aluminum casting for maximum shielding and rigidity. The stan-

dard unit consists of five helical resonators, 1st mixer, oscillator and two multiplier stages, and a high IF amplifier.

An optional RF pre-amplifier stage is available whenever an increase in sensitivity is required. The chassis is mounted in a housing on the rear of the mobile frame, adding approximately three inches to the overall length of the mobile unit. A block diagram of the DFE is shown in Figure 1.

ANTENNA SYSTEM

The Dual Front End and the receiver use a common antenna. A power splitter mounted on the front of the system frame provides approximately 20 dB separation for the two receive channels. Due to the isolation provided by the power splitter, cable lengths to the DFE and the receiver are not critical.

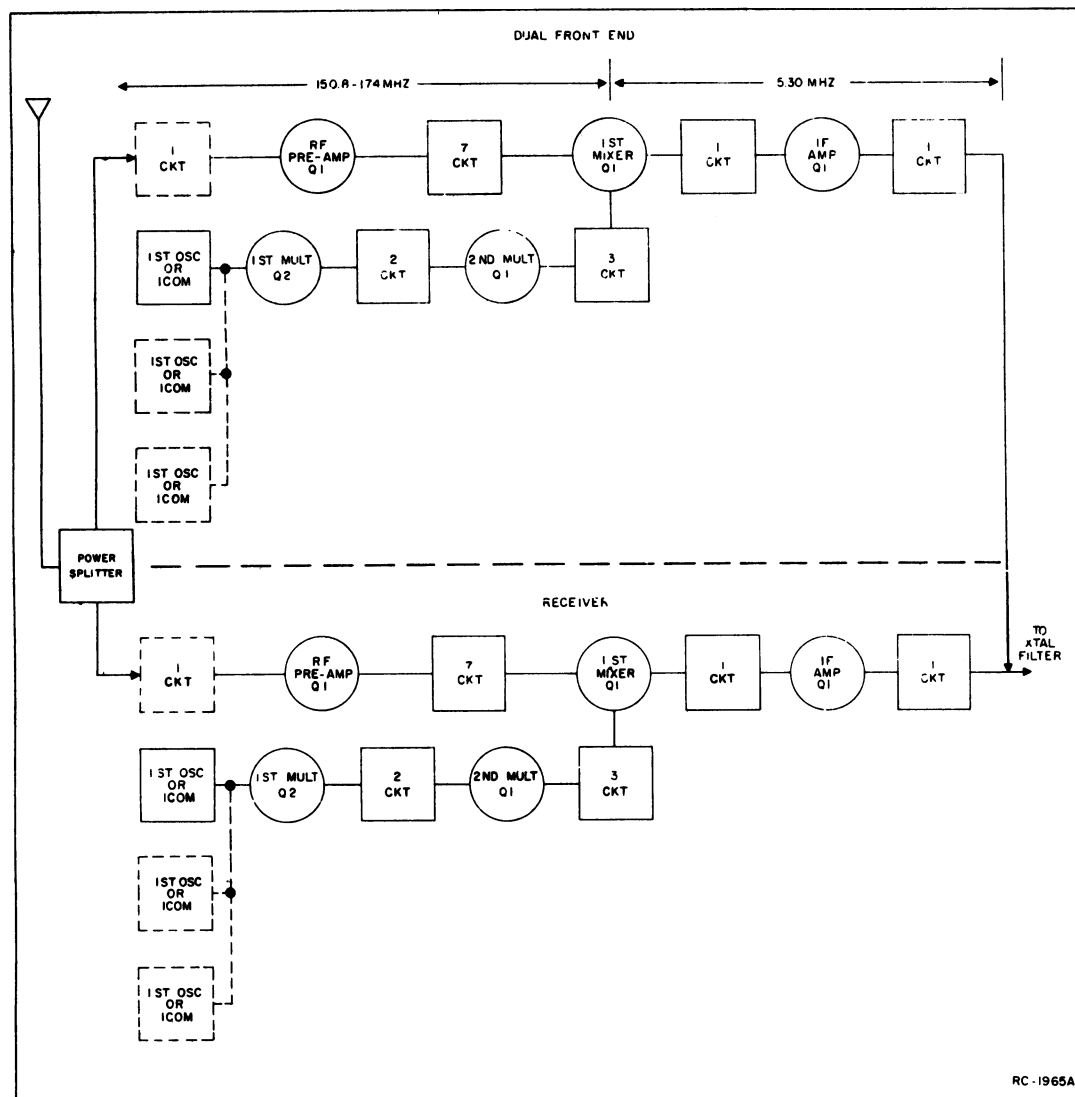


Figure 1 - Dual Front End Block Diagram

In standard applications, the antenna connects to J901 on the front of the mobile unit. From J901, the antenna connects to the common terminal of the antenna relay (see Figure 2). The transmitter connects to the normally-open contact on the antenna relay, while the normally-closed contact is connected to input jack J3 on the power splitter.

One cable from the power splitter connects to the DFE input jack (J2/J2357), and the other cable connects to J441 on the receiver.

CIRCUIT ANALYSIS

DUAL FRONT END

The MASTR Progress Line Dual Front End is completely transistorized, using six silicon transistors. A regulated 10 volts is used for all stages of the Dual Front End.

Centralized metering jack J2351 is provided for use with GE Test Set Models 4EX3A10 and 4EX8K11 for ease of alignment and servicing. The Test Set meters the oscillator, multipliers, and the regulated 10 volts.

The regulated 10 volts, oscillator keying voltages system negative, and ground connections are supplied by the two cables from receiver plug P443.

RF Preamplifier (A2372)

Optional RF Preamplifier A2372 consists of RF Amplifier Q1 and associated components.

The preamplifier uses a dual gate MOS FET as the active device. The MOS FET may be considered a semiconductor current path (or channel) whose resistance is varied by a voltage applied between the "gate" and "source" terminals.

RF from the antenna is coupled through C1 to Gate 1 terminal of MOS FET Q1. Q1 operates as a grounded-gate amplifier. This method of operation provides a low impedance input to the amplifier. The amplified output is taken from the "drain" terminal and coupled through C6 to the input of five helical resonators.

Helical Resonators

Five tuned helical resonators L2352 through L2360 provide the RF selectivity in the dual front end. An RF cable connects the RF signal from the antenna or the optional Pre-amp to a tap on L2352. The tap is positioned to provide the proper impedance match to the antenna. The output of L2360 is coupled through C3 to the 1st mixer assembly.

Standard Oscillator/Multiplier (A2358)

The standard 1st oscillator operates in a transistorized Colpitts oscillator circuit. The oscillator crystal operates in a funda-

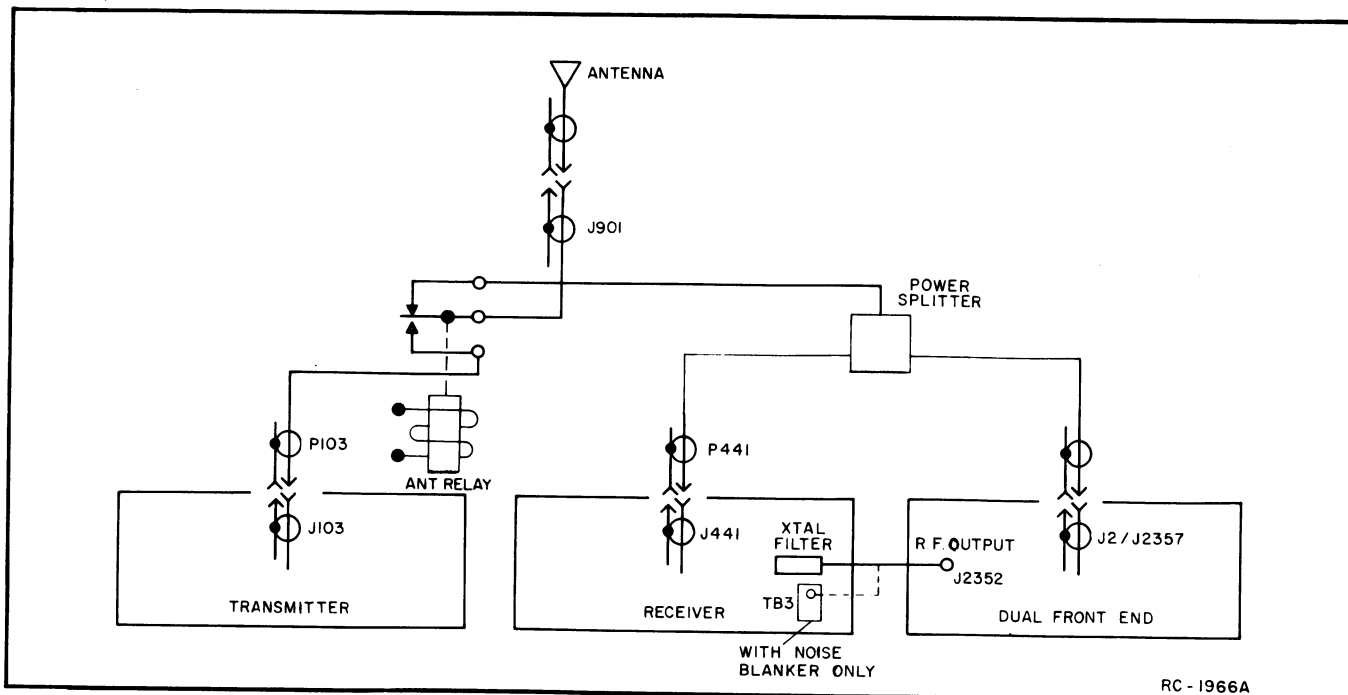


Figure 2 - Single Antenna Block Diagram

mental mode at a frequency of approximately 13 to 18 megahertz. The crystal is cut to provide temperature compensation at the high end of the temperature range and is thermistor compensated at low temperatures. This provides $\pm 0.0005\%$ frequency stability as soon as the power is applied -- without having to wait for crystal ovens to warm up.

A four-frequency 1st oscillator/multiplier board is provided with the DFE. The proper frequency is selected by switching the desired crystal circuit to +10 volts by means of a frequency selector switch on the control unit. See Figure 3 for the available frequency combinations.

Receiver	
1 Freq.	1 Freq.
1 Freq.	2 Freq.
1 Freq.	3 Freq.
2 Freq.	1 Freq.
2 Freq.	2 Freq.
3 Freq.	1 Freq.

Figure 3 - Frequency Combinations

Regulated 10 volts is supplied to the crystal circuit to forward bias one of the four diodes CR1-CR4. Forward biasing the diode reduces its impedance, so that the crystal frequency is applied to the base of oscillator transistor Q1. Feedback for the oscillator is developed across C21. The oscillator output is coupled through C24 to the base of 1st multiplier Q2.

The output of the 1st multiplier (trippler Q2) is transformer-coupled (T2) to the 2nd multiplier assembly. The 1st multiplier is tuned to three times the crystal frequency, and is metered at centralized metering jack J2351-4 through metering network CR5, R5, R16 and C32.

Oscillator Multiplier With ICOM (A2362)

Oscillator/Multiplier Board A2362 uses ICOM Module Model 4EG26A11. The ICOM Module consists of a crystal-controlled Colpitts oscillator, a voltage regulator and a buffer output stage. The entire module (including crystal) is enclosed in a dust-proof aluminum can, with the ICOM frequency and the receiver operating frequency printed on the top. Access to the oscillator trimmer is obtained by prying off the plastic GE decal on the top of the can.

The oscillator frequency is temperature-compensated at both ends of the temperature

range to provide instant frequency compensation, with a frequency stability of $\pm 0.0002\%$ without crystal ovens or warmers.

A four-frequency 1st oscillator/multiplier board is provided with the DFE. The proper frequency is selected by switching the desired ICOM circuit to +10 volts by means of a frequency selector switch on the control unit. See Figure 3 for the available frequency combinations.

In the DFE, +10 volts for operating the ICOM is obtained through the frequency selector switch on the control unit. With the ICOM operating, one of the four diodes CR1-CR4 is forward biased and the oscillator output is applied to 1st multiplier Q1.

The output of the 1st multiplier (trippler) is transformer-coupled (T2) to the 2nd multiplier assembly. The 1st multiplier tank is tuned to three times the crystal frequency, and is metered at centralized metering jack J442-4 through metering network CR5, R16, R5 and C33.

2nd Multiplier (A2354)

The 1st multiplier output is transformer coupled through T2 to the base of 2nd multiplier A2354-Q1. Following the 2nd multiplier are three resonant L-C circuits tuned to nine times the crystal frequency. The output is taken from a tap on L2362 and applied to the 1st mixer.

1st Mixer (A2352)

The 1st mixer uses a Field-Effect Transistor (FET) as the active device. The FET may be considered a semiconductor current path (or channel) whose resistance is varied by a voltage applied between the "gate" and "source" terminals. Lead identification for the FET is shown in Figure 4. The FET has voltage-controlled characteristics, and may be compared to a vacuum tube in operation (see Figure 4).

The FET has several advantages over a conventional transistor, including a high input impedance, high power gain, and an output that is relatively free of harmonics (low in intermodulation products).

In the 1st mixer, RF from the helical resonators is applied to the gate of Q1, and injection voltage from the 2nd multiplier is applied to the source. The mixer output is taken from the drain and applied to the output transformer. The transformer is tuned to the 5.3 MHz high IF frequency.

HI IF Amplifier (A2365)

A series-resonant circuit (L3 and C1) couples the mixer output to the emitter of high IF amplifier Q1. The transistor operates as a grounded-base amplifier which provides a low impedance for the mixer input. The amplifier output is coupled through transformer T1 to the crystal filter

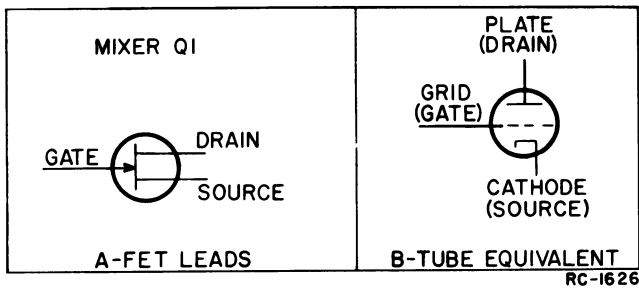


Figure 4 - FET Nomenclature

on standard receivers and to the level switch and IF gate on receiver with Noise Blanker.

Diode Assembly 19B219305G1

The Diode Assembly 19B219305G1 is used only with 150.8-174 MHz Receivers and Dual Front Ends. The purpose of the diode assembly is to turn off the HI IF Amplifier and 1st Mixer of the receiver or DFE when the other is operating. Refer to Figure 5 for a typical Diode Assembly connection. Because of the many frequency combinations as shown in figure 3, the diode assembly consists of three diodes. All unused diodes are removed.

RECEIVER MODIFICATIONS

The following modification is required in the MASTR mobile receiver whenever the receiver is used with a Dual Front End option.

1. In receivers without Noise Blankers:

- a. Replaced the 5.6K-ohm resistor across the input of Crystal Filter A316 with a 12K-ohm resistor (GE Part No. 3R77-P123K).
- b. Connected the center conductor of DFE output cable 19A127259G1 to the filter input, and the shield to the ground lug on the filter.

2. In receiver with Noise Blankers, connected the center conductor of the DFE output cable to TB3-2 and the shield to TB3-1.

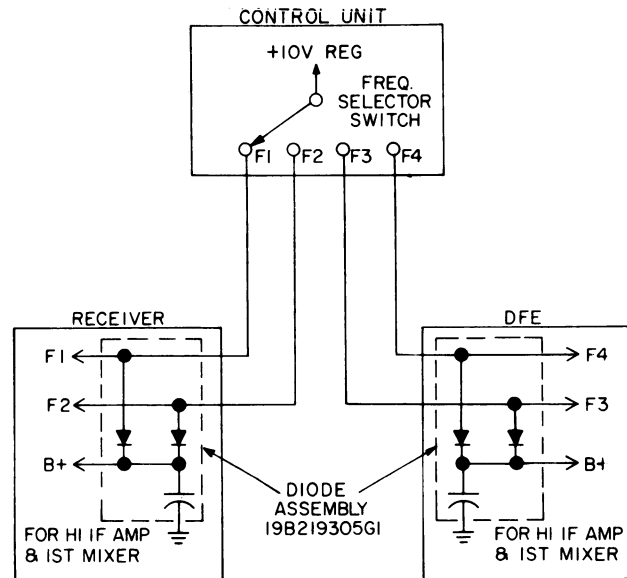


Figure 5 - Typical Diode Assembly Connection

3. Soldered the leads from cables 19B204924G1 and 19B219302G1 to P443 as shown on the Outline Diagram (see Table of Contents).
4. Connected RF cable from the Power Splitter to J441.
5. Connect diode assembly to 1st Osc./Mult. (see Table of Contents).

MAINTENANCE

DISASSEMBLY

To gain access to the DFE:

1. Pull locking handle down and pull radio out of mounting frame.
2. Remove the four screws holding back cover to system frame. Slide cover back and lift off (see Figure 6).
3. Remove four screws from angle brackets holding Dual Front End to the system frame.

INSTRUCTIONS FOR CHANGING FREQUENCIES
WHEN THE DIODE ASSEMBLY IS USED

GENERAL

1. To increase the number of frequencies on the Receiver or the Dual Front End. A new Diode Assembly will have to be ordered for each one or both as the case may be.
2. The diodes will be connected only to the jacks that have crystals in the respective crystal sockets.
3. There will be no more than one crystal per frequency in the receiver and Dual Front End combined.

PROCEDURE

1. Select the desired frequency combination and get the connection table from the following chart:

No. of Receiver Freq.	No. of DFE Freq.	Table
1	1	A
1	2	B
1	3	C
2	1	D
2	2	E
3	1	F

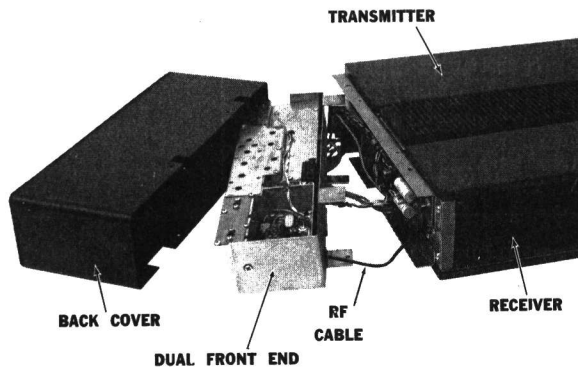


Figure 6 - Dual Front End Disassembly

4. Carefully swing Dual Front End chassis out for servicing.

TEST PROCEDURES

Dual Front End

SYMPTOM	CHECK
No Output	<ol style="list-style-type: none"> 1. Connections to P443. 2. Cable from J2352 to receiver mixer board. 3. Antenna terminal connections. 4. Check 10-volt supply with GE test meter at Pin 13 on DFE centralized metering jack J2351.
Low Sensitivity	<ol style="list-style-type: none"> 1. DFE alignment. 2. Cable and relay connections. 3. 1st Mixer voltages. 4. 1st Oscillator voltages. 5. HI IF Amplifier voltages.
Low Oscillator Reading	<ol style="list-style-type: none"> 1. Oscillator alignment. 2. Voltage readings at 1st oscillator. 3. Crystals Y1, Y2, Y3.

2. Unplug all the oscillator keying leads on the receiver and dual front end.
3. Refer to the table found in Step 1. Connect the loose end(s) of the diode(s) as follows: For the receiver, find the row that has the connections for the frequency or frequencies desired. Follow the same row across for the proper Dual Front End connection(s).
4. Clip off all unused diodes.
5. Replace the oscillator keying leads removed in step 2. Connect as shown below:

White - Yellow - Brown	to J5
White - Yellow - Red	to J4
White - Yellow - Orange	to J3
White - Yellow - Green	to J6

TABLE A

ROW	1-Freq. Receiver				1-Freq. DUAL FRONT END			
	F1	F2	F3	F4	F1	F2	F3	F4
1	J5					J4		
2		J4			J5			

TABLE B

ROW	1-Freq. Receiver				2-Freq. DUAL FRONT END			
	F1	F2	F3	F4	F1	F2	F3	F4
1	J5					J4	J3	
2			J3		J5	J4		

TABLE C

ROW	1-Freq. Receiver				3-Freq. DUAL FRONT END			
	F1	F2	F3	F4	F1	F2	F3	F4
1	J5					J4	J3	J6
2				J6	J5	J4	J3	

TABLE D

ROW	2-Freq. Receiver				1-Freq. DUAL FRONT END			
	F1	F2	F3	F4	F1	F2	F3	F4
1	J5	J4					J3	
2		J4	J3		J5			
3	J5		J3			J4		

TABLE E

ROW	2-Freq. Receiver				2-Freq. DUAL FRONT END			
	F1	F2	F3	F4	F1	F2	F3	F4
1	J5	J4					J3	J6
2		J4	J3		J5			J6
3			J3	J6	J5	J4		
4	J5			J6		J4	J3	
5	J5		J3			J4		J6

TABLE F

ROW	3-Freq. Receiver				1-Freq. DUAL FRONT END			
	F1	F2	F3	F4	F1	F2	F3	F4
1	J5	J4	J3					J6
2		J4	J3	J6	J5			
3	J5		J3	J6		J4		
4	J5	J4		J6			J3	

GENERAL ELECTRIC COMPANY • MOBILE COMMUNICATIONS DIVISION
WORLD HEADQUARTERS • LYNCHBURG, VIRGINIA 24502 U.S.A.

GENERAL ELECTRIC*
U.S.A.

ICOM FREQUENCY ADJUSTMENT

Due to the high stability of the ICOM module, it is not recommended that zero discriminator be used as the indication for setting the oscillator frequency. Instead, measure the ICOM frequency as described in the following procedure.

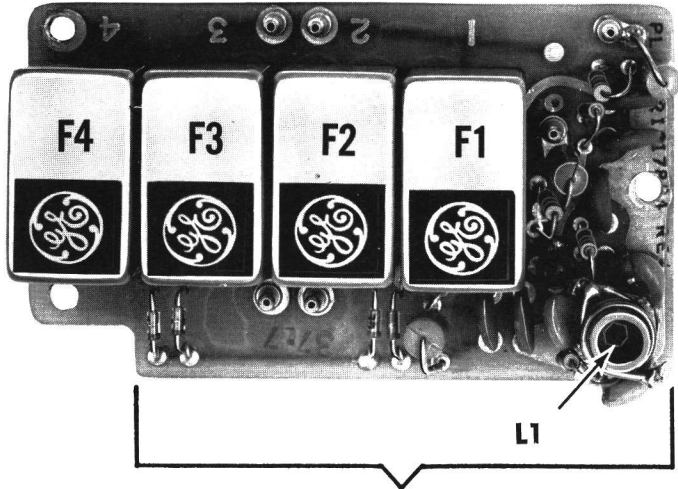
EQUIPMENT REQUIRED:

- 1. Frequency Counter capable of measuring the 42 to 56.25 MHz frequency range. The counter should have an accuracy of 0.4 part-per million (PPM).
- 2. Coaxial cable with test loop as described in Figure 7.
- 3. Mercury thermometer.

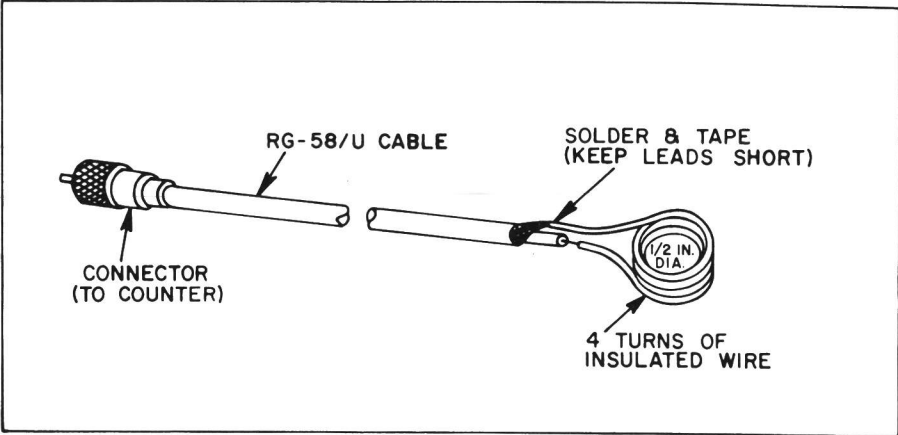
PROCEDURE:

- 1. Check ICOM temperature by taping the mercury thermometer to the side of the ICOM.
- 2. Connect the coaxial cable to the frequency counter. Then place the 4-turn test loop over L1 on the 1st OSC/MULT board.
- 3. If the ICOM temperature is 80°F (±4°F) or 26.5°C (±2°C), the frequency indication on the counter should be 3 times the frequency stenciled on the ICOM case. Adjust the ICOM trimmer (if necessary) to obtain this frequency.
- 4. If the temperature is not within the 80°F (±4°F) or 26.5°C (±2°C) range, use the correction curves of Figure 8 for setting the ICOM frequency as follows:
 - a. Check the color dot beneath the GE emblem and select the matching curve to determine the correction factor in parts-per-million (PPM).
 - b. Multiply the frequency stenciled on the ICOM by 3 and then multiply this figure by the correction factor (from Figure 8) observing the sign (±) given to the correction factor.
 - c. The frequency measured at L1 should be 3 times the ICOM frequency ± the correction factor. Adjust the ICOM trimmer (if required) to obtain this frequency.

EXAMPLE		
ICOM Frequency	-	16.948,148 MHz
ICOM Color Dot	-	Green
Ambient Temperature	-	35°C (95°F)
Correction Factor	-	-1.15 PPM
Multiply ICOM Frequency by 3; (16.948,148 MHz x 3 = 50.844,444 MHz)		
Multiply preceding figure by correction factor; (50.844 MHz x -1.15 PPM = 58.47 hertz (or -58 hertz)		
Set the frequency measured at L1 for 50.844,386 MHz;		
50.844,444		
- 58		
50.844,386		

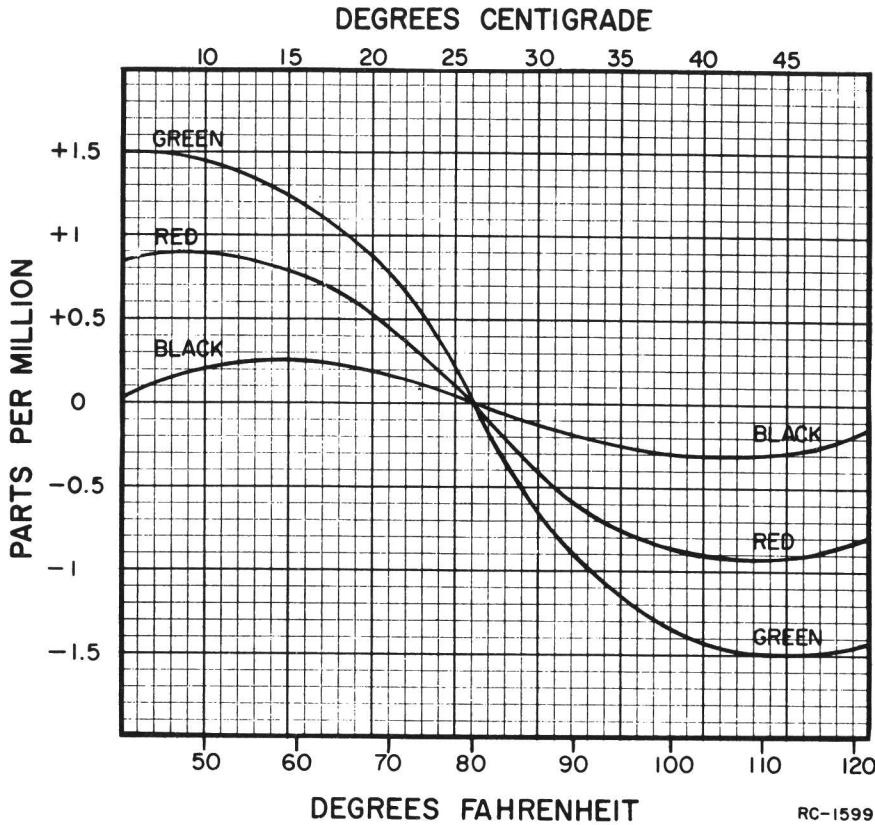


1st OSC./MULT. WITH ICOMS



RC-1779

Figure 7 - Coaxial Cable and Test Loop



RC-1599

Figure 8 - ICOM Correction Curves

ADJUSTMENT PROCEDURE

ICOM ADJUSTMENT

DUAL FRONT END ALIGNMENTS

Refer to Receiver MAINTENANCE MANUAL for Receiver IF Alignment Procedure.

EQUIPMENT REQUIRED

- 1. GE Test Set Models 4EX3A10 or 4EX8K11 (or a 20,000 ohm-per-volt multi-meter).
- 2. Signal Generator (150.8-174 MHz range). Connect a one-inch piece of insulated wire no larger than .065-inch diameter to generator output probe.

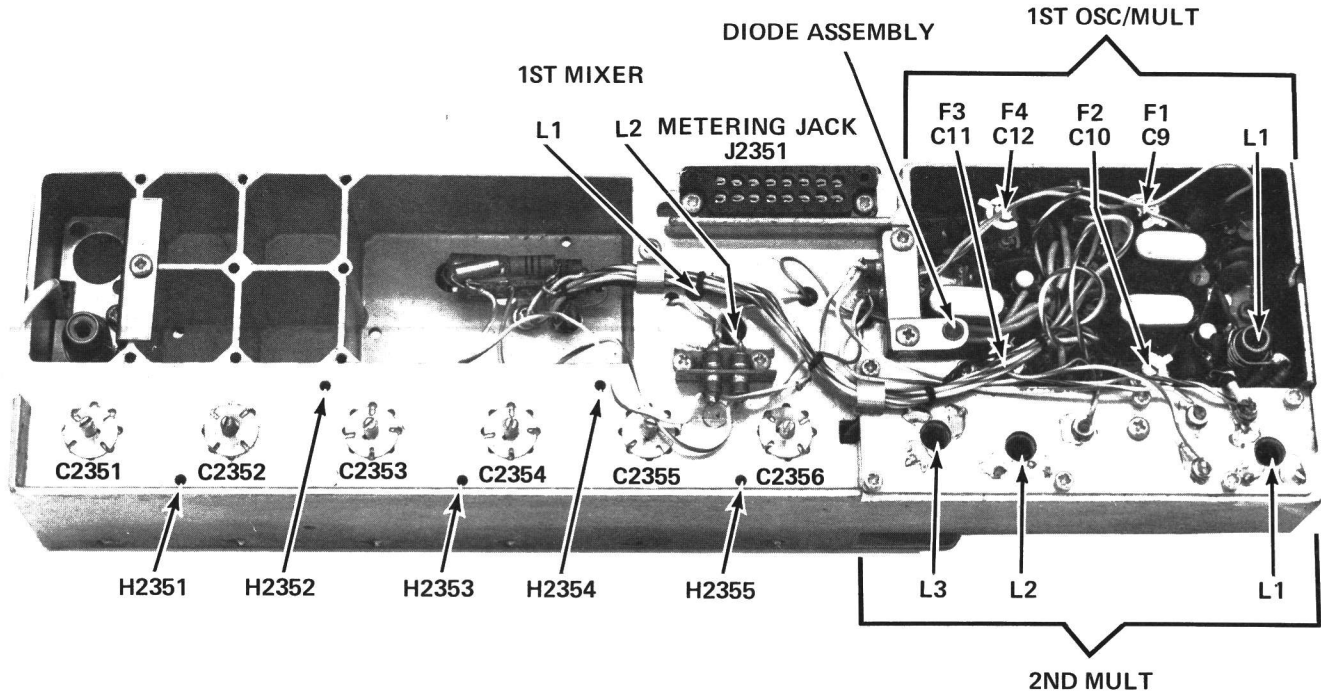
PRELIMINARY CHECKS AND ADJUSTMENTS

- 1. Plug Test Set cable into metering jack J2351. With Test Set in position J, check for regulated +10 volts. If using multimeter, measure at metering jack J2351-13 and -16.
- 2. If using Multimeter for alignment, connect positive lead to J2351-16 (ground).
- 3. Set the frequency selector switch on the control unit to select the center frequency of the multi-frequency DFE.
- 4. For a large change in frequency or a badly mis-aligned DFE, set crystal trimmers C9, C10, C11 & C12 on standard 1st Osc/Mult board to mid-capacity. Do not touch ICOM trimmers if using ICOM oscillators.

ALIGNMENT PROCEDURE

LB1-4241

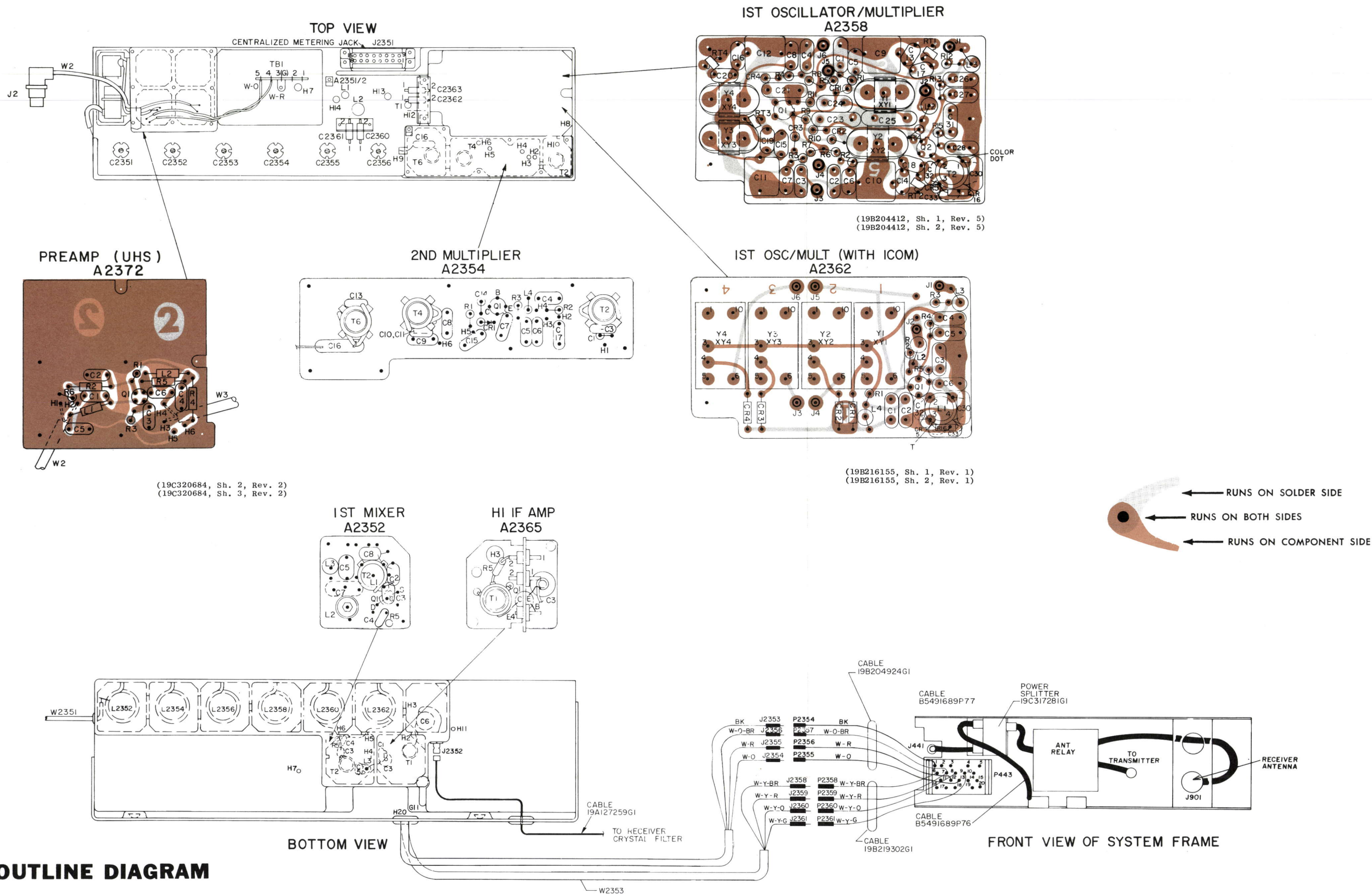
STEP	METERING POSITION		TUNING CONTROL	METER READING	PROCEDURE
	GE Test Set	Multimeter - at J2351			
OSCILLATOR, MULTIPLIERS & 1ST MIXER					
1.	D (Mult 1 on DFE)	Pin 4	L1 (on 1st OSC/MULT), and L1 (on 2nd MULT)	See Procedure	Switch Test Set to Test 1 or 1-volt position. Tune L1 on 1st OSC/MULT for maximum meter reading. Then tune L1 on 2nd Mult for minimum meter reading.
2.	E (Mult 2 on DFE)	Pin 5	L1 (on 1st OSC/MULT), and L1, L2 and L3 (on 2nd MULT)	See Procedure	Tune L1 on 1st OSC/MULT and L1 and L2 on 2nd MULT for maximum meter reading. Then tune L3 for minimum meter reading.
3.	A (Disc on Receiver)	Pin 10		Zero	Connect Test Set plug to receiver metering jack J442. Insert signal generator probe into H2355 and adjust signal generator for discriminator zero.
4.	B (2nd IF Amp on Receiver)	Pin 2	L1 and L2 (on 1st Mixer)	Maximum	Apply an on-frequency signal as above. Tune L1 and L2 for maximum meter reading, keeping signal below saturation.
RF CIRCUITS					
5.	B (2nd IF Amp on Receiver)	Pin 2	C2356, C2355, C2354, C2353 and C2352	Maximum	Apply an on-frequency signal into the holes as shown below. Insert probe into hole only deep enough to obtain a reading. <div><div>Insert Probe Into:</div><div>Tune:</div><div><div>1. H2355</div><div>C2356</div><div>2. H2354</div><div>C2355</div><div>3. H2353</div><div>C2354</div><div>4. H2352</div><div>C2353</div><div>5. H2351</div><div>C2352</div></div></div>
6.	B (2nd IF Amp on Receiver)	Pin 2	C2351 thru C2356	See Procedure	Apply an on-frequency signal to the DFE antenna jack. On all DFE's tune C2351 thru C2356 for maximum meter reading, keeping signal below saturation. Then return C2351 thru C2356 slightly for maximum quieting.
FREQUENCY ADJUSTMENT (Standard Oscillator)					
7.	A (Disc on Receiver)	Pin 10	C9 (on 1st OSC/MULT) (C10, C11 and C12 for multi-frequency)	Zero	Apply an on-frequency signal to the DFE antenna jack. Tune C9 for zero discriminator reading. In multi-frequency units tune C10, C11 or C12 as required. - NOTE - For proper frequency control of the receiver, it is recommended that all frequency adjustments be made when the equipment is at a temperature of approximately 75°F. In no case should frequency adjustments be made when the equipment is outside the temperature range of 50° to 90°F.



ALIGNMENT PROCEDURE

150.8—174 MHz, DUAL FRONT END
MODEL 19D413462 G1

(DF-8401)



PARTS LIST		
LBI4242D		
150.8-174 MHz DUAL FRONT END 19D413462G1		
SYMBOL	GE PART NO.	DESCRIPTION
A2352		FIRST MIXER 19B216077G2
----- CAPACITORS -----		
C2		(Part of T2).
C3		(Part of T2).
C4	5494481P11	Ceramic disc: 1000 pf ±20%, 1000 VDCW; sim to RMC Type JF Discap.
C5	5494481P112	Ceramic disc: 1000 pf ±10%, 1000 VDCW; sim to RMC Type JF Discap.
C7	7489162P35	Silver mica: 220 pf ±5%, 500 VDCW; sim to Electro Motive Type DM-15.
C8	5496203P149	Ceramic disc: 220 pf ±10%, 500 VDCW, temp coef -3300 PPM.
C9	5491601P130	Phenolic: 3.3 pf ±5%, 500 VDCW.
----- INDUCTORS -----		
L1		(Part of T2).
L2	19B216579G1	Coil.
L3	7488079P6	Choke, RF: 1 µh ±10%, 0.3 ohm DC res max; sim to Jeffers 4411-8K.
----- TRANSISTORS -----		
Q1*	19A116960P1	N Type, field effect; sim to Type 2N4416.
In REV D & earlier:		
19A116154P1		N Channel, field effect.
----- RESISTORS -----		
R1	3R152P242J	Composition: 2.4K ohms ±5%, 1/4 w.
R2	3R152P101K	Composition: 100 ohms ±10%, 1/4 w.
R4	3R152P101K	Composition: 100 ohms ±10%, 1/4 w.
R5	3R77P331K	Composition: 330 ohms ±10%, 1/2 w.
R6		(Part of T2).
----- TRANSFORMERS -----		
T2		COIL ASSEMBLY 19B216100G2
----- CAPACITORS -----		
C2	5496218P234	Ceramic disc: 3.0 pf ±0.25 pf, 500 VDCW; temp coef -80 PPM.
C3	5494481P11	Ceramic disc: 1000 pf ±20%, 1000 VDCW; sim to RMC Type JF Discap.
----- INDUCTORS -----		
L1	19B216100P6	Coil.
----- RESISTORS -----		
R6*	3R152P103K	Composition: 10K ohms ±10%, 1/4 w. Added by REV C.
19B209674P28		Tuning slug.
A2354*		SECOND MULTIPLIER 19B219908G2
----- CAPACITORS -----		
C1	5491601P107	Phenolic: 0.27 pf ±5%, 500 VDCW.
C3		(Part of T2).

SYMBOL	GE PART NO.	DESCRIPTION
C4	5496203P133	Ceramic disc: 100 pf ±10%, 500 VDCW, temp coef -3300 PPM.
C5	5494481P11	Ceramic disc: 1000 pf ±20%, 1000 VDCW; sim to RMC Type JF Discap.
C6	19A116080P105	Polyester: 0.047 µf ±10%, 50 VDCW.
C7	5494481P11	Ceramic disc: 1000 pf ±20%, 1000 VDCW; sim to RMC Type JF Discap.
C8	19A116080P105	Polyester: 0.047 µf ±10%, 50 VDCW.
C9	5494481P11	Ceramic disc: 1000 pf ±20%, 1000 VDCW; sim to RMC Type JF Discap.
C11		(Part of T4).
C13		(Part of T6).
C14	5491601P16	Phenolic: 0.62 pf ±10%, 500 VDCW.
C15	5494481P11	Ceramic disc: 1000 pf ±20%, 1000 VDCW; sim to RMC Type JF Discap.
C16		(Part of T6).
C17	5494481P11	Ceramic disc: 1000 pf ±20%, 1000 VDCW; sim to RMC Type JF Discap.
CR1	19A115250P1	Silicon, fast recovery, 225 mA, 50 PIV.
----- INDUCTORS -----		
L1		(Part of T2).
L2		(Part of T4).
L3		(Part of T6).
L4	19B209420P111	Coil, RF: 0.68 µh ±10%, 0.54 ohms DC res max; sim to Jeffers 4426-4K.
----- TRANSISTORS -----		
Q1	19A115440P1	Silicon, NPN.
----- RESISTORS -----		
R1	3R152P103K	Composition: 10K ohms ±10%, 1/4 w.
R2	3R152P104K	Composition: 100K ohms ±10%, 1/4 w.
R3	3R152P101K	Composition: 100 ohms ±10%, 1/4 w.
----- TRANSFORMERS -----		
T2		COIL ASSEMBLY 19B216097G4
----- CAPACITORS -----		
C3	5496218P252	Ceramic disc: 36 pf ±5%, 500 VDCW, temp coef -80 PPM.
----- INDUCTORS -----		
L1	19B216097P6 19B209674P25	Coil. Tuning slug.
T4		COIL ASSEMBLY 19B216108G4
----- CAPACITORS -----		
C11	5496218P238	Ceramic disc: 7.0 pf ±0.25 pf, 500 VDCW, temp coef -80 PPM.
----- INDUCTORS -----		
L2	19B216106P6 19B209674P25	Coil. Tuning slug.
T6		COIL ASSEMBLY 19B216102G2
----- CAPACITORS -----		
C13	5496218P239	Ceramic disc: 8.0 pf ±0.25 pf, 500 VDCW, temp coef -80 PPM.

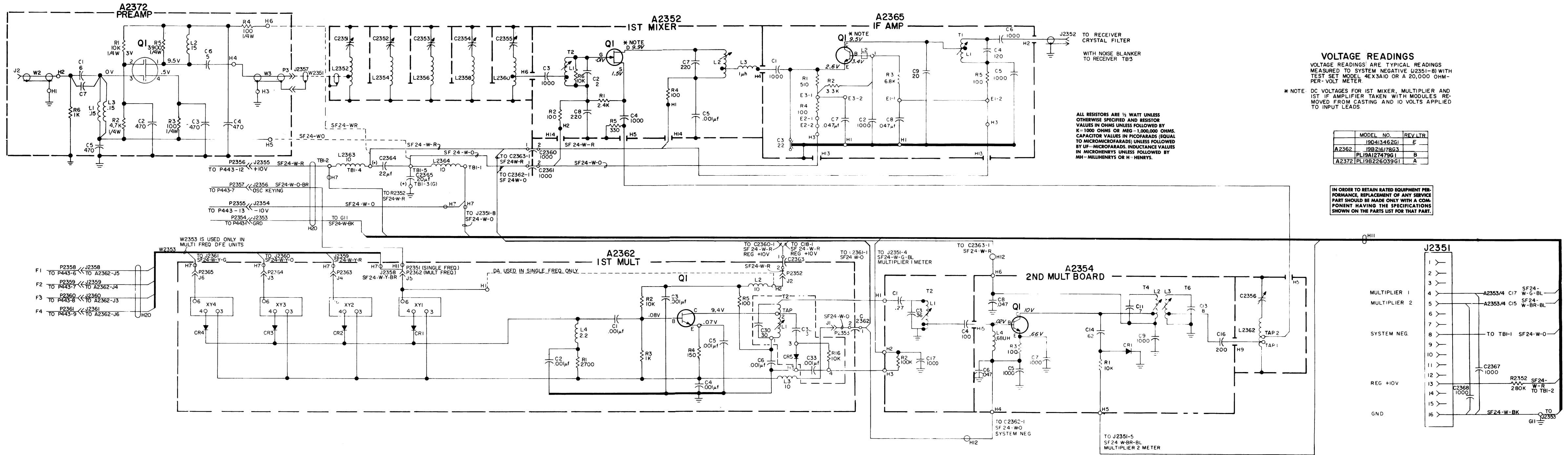
SYMBOL	GE PART NO.	DESCRIPTION
C16	5496218P770	Ceramic disc: 200 pf ±5%, 500 VDCW, temp coef -750 PPM.
----- INDUCTORS -----		
L3	19B216102P6 19B209674P25	Coil. Tuning slug.
In REV C & earlier:		
A2354*		SECOND MULTIPLIER 19B216107G2
----- CAPACITORS -----		
C1		(Part of T2).
C3		(Part of T2).
C4		(Part of T2).
C5	5493392P7	Ceramic, feed-thru: 1000 pf +100%-0%, 500 VDCW; sim to Allen Bradley Type FASC.
C6	19A116080P105	Polyester: 0.047 µf ±10%, 50 VDCW.
C7	5494481P11	Ceramic disc: 1000 pf ±20%, 1000 VDCW; sim to RMC Type JF Discap.
C8	19A116080P105	Polyester: 0.047 µf ±10%, 50 VDCW.
C9		(Part of T4).
C11		(Part of T4).
C13		(Part of T6).
C14	5491601P16	Phenolic: 0.62 pf ±10%, 500 VDCW.
C15	5493392P7	Ceramic, feed-thru: 1000 pf +100%-0%, 500 VDCW; sim to Allen Bradley Type FASC.
C16		(Part of T6).
C17 and C18	5493392P7	Ceramic, feed-thru: 1000 pf +100%-0%, 500 VDCW; sim to Allen Bradley Type FASC.
----- INDUCTORS -----		
L1		(Part of T2).
L2		(Part of T4).
L3		(Part of T6).
L4*	19B209420P111	Coil, RF: 0.68 µh ±10%, 0.54 ohms DC res max; sim to Jeffers 4426-4K. Added by REV C.
----- TRANSISTORS -----		
Q1*	19A115440P1	Silicon, NPN.
----- RESISTORS -----		
R1*	3R152P392K	Composition: 3.9K ohms ±10%, 1/4 w. Deleted by REV C.
R2*	3R152P103K	Composition: 10K ohms ±10%, 1/4 w. Deleted by REV C.
R3*	3R152P101K	Composition: 100 ohms ±10%, 1/4 w.
In REV B & earlier:		
3R152P331K		Composition: 330 ohms ±10%, 1/4 w.
R4	3R152P103K	Composition: 10K ohms ±10%, 1/4 w.
R5	3R152P104K	Composition: 100K ohms ±10%, 1/4 w.
----- TRANSFORMERS -----		
T2		COIL ASSEMBLY 19B216097G2
----- CAPACITORS -----		
C1	5491601P107	Phenolic: 0.27 pf ±5%, 500 VDCW.
C3	5496218P252	Ceramic disc: 36 pf ±5%, 500 VDCW, temp coef -80 PPM.
C4	5496203P133	Ceramic disc: 100 pf ±10%, 500 VDCW, temp coef -3300 PPM.

SYMBOL	GE PART NO.	DESCRIPTION
----- INDUCTORS -----		
L1	19B216097P6 5491798P5	Coil. Tuning slug.
T4		COIL ASSEMBLY 19B216106G2
----- CAPACITORS -----		
C9	5494481P11	Ceramic disc: 1000 pf ±20%, 1000 VDCW; sim to RMC Type JF Discap.
C11	5496218P238	Ceramic disc: 7.0 pf ±0.25 pf, 500 VDCW, temp coef -80 PPM.
----- DIODES AND RECTIFIERS -----		
CR1	19A115250P1	Silicon.
----- INDUCTORS -----		
L2	19B216106P6 5491798P5	Coil. Tuning slug.
T6		COIL ASSEMBLY 19B216102G2
----- CAPACITORS -----		
C13	5496218P239	Ceramic disc: 8.0 pf ±0.25 pf, 500 VDCW, temp coef -80 PPM.
C16	5496218P770	Ceramic disc: 200 pf ±5%, 500 VDCW, temp coef -750 PPM.
----- INDUCTORS -----		
L3	19B216102P6 5491798P5	Coil. Tuning slug.
----- THERMISTORS -----		
RT1 thru RT4	19B209284P5	Disc: 43 ohms nominal, color code green.
----- TERMINAL BOARDS -----		
TB1	7487424P7	Miniature, phen: 4 terminals.
A2358		FIRST OSCILLATOR 19B204419G6
----- CAPACITORS -----		
C1 thru C4	5494481P112	Ceramic disc: 1000 pf ±10%, 1000 VDCW; sim to RMC Type JF Discap.
C5 thru C8	5496219P751	Ceramic disc: 33 pf ±5%, 500 VDCW, temp coef -750 PPM.
C9 thru C12	5491271P106	Variable, subminiature: approx 2.1-12.7 pf 750 v peak; sim to EF Johnson 189.
C13 thru C16	5496219P40	Ceramic disc: 9 pf ±0.25 pf, 500 VDCW, temp coef 0 PPM.
C17 thru C20	19C300685P93	Ceramic disc: 5 pf ±0.1 pf, 500 VDCW, temp coef 0 PPM.
C21	5496219P771	Ceramic disc: 220 pf ±5%, 500 VDCW, temp coef -750 PPM.
C23	5494481P114	Ceramic disc: 2000 pf ±10%, 1000 VDCW; sim to RMC Type JF Discap.
C24	5490008P31	Silver mica: 150 pf ±5%, 500 VDCW; sim to Electro Motive Type DM-15.
C25	5496219P467	Ceramic disc: 150 pf ±5%, 500 VDCW, temp coef -220 PPM.
C26 thru C28	5494481P112	Ceramic disc: 1000 pf ±10%, 1000 VDCW; sim to RMC Type JF Discap.
C30		(Part of T2).
C31	5494481P112	Ceramic disc: 1000 pf ±10%, 1000 VDCW; sim to RMC Type JF Discap.
----- DIODES AND RECTIFIERS -----		
CR1 thru CR4	19A115603P1	Silicon.
CR5		(Part of T2).

SYMBOL	GE PART NO.	DESCRIPTION
----- JACKS AND RECEPTACLES -----		
J1 thru J6	4033513P4	Contact, electrical: sim to Bead Chain L93-3.
----- INDUCTORS -----		
L1		(Part of T2).
L2 and L3	7488079P16	Choke, RF: 10 µh ±10%, 0.6 ohm DC res; sim to Jeffers 4421-7K.
----- TRANSISTORS -----		
Q1 and Q2	19A115330P1	Silicon, NPN.
----- RESISTORS -----		
R1 thru R4	3R152P582J	Composition: 5.6K ohms ±5%, 1/4 w.
R5 thru R8	3R152P104K	Composition: 100K ohms ±10%, 1/4 w.
R9	3R152P153J	Composition: 15K ohms ±5%, 1/4 w.
R10	3R152P101K	Composition: 100 ohms ±10%, 1/4 w.
R11 and R12	3R152P102J	Composition: 1K ohms ±5%, 1/4 w.
R13	3R152P151J	Composition: 150 ohms ±5%, 1/4 w.
R14	3R152P103J	Composition: 10K ohms ±5%, 1/4 w.
R15	3R152P101K	Composition: 100 ohms ±10%, 1/4 w.
R16		(Part of T2).
----- THERMISTORS -----		
RT1 thru RT4	19B209284P5	Disc: 43 ohms nominal, color code green.
----- TRANSFORMERS -----		
T2		COIL ASSEMBLY 19B204421G2
----- CAPACITORS -----		
C30	5496218P250	Ceramic disc: 30 pf ±5%, 500 VDCW, temp coef -80 PPM.
C32	5496218P34	Ceramic disc: 3 pf ±0.25 pf, 500 VDCW, temp coef 0 PPM.
C33	5494481P12	Ceramic disc: 1000 pf ±10%, 1000 VDCW; sim to RMC Type JF Discap.
----- DIODES AND RECTIFIERS -----		
CR5	19A115250P1	Silicon, fast recovery, 225 mA, 50 PIV.
----- INDUCTORS -----		
L1	19A121093P1	Coil.
----- RESISTORS -----		
R16	3R152P103K 19B209674P25	Composition: 10K ohms ±10%, 1/4 w. Tuning slug.
----- SOCKETS -----		
XY1 thru XY4		Refer to Mechanical Parts (RCL637).
----- CRYSTALS -----		
C26 thru C28	5494481P112	Ceramic disc: 1000 pf ±10%, 1000 VDCW; sim to RMC Type JF Discap.
C30		NOTE: When reordering give GE Part No. and specify exact freq needed.
C31	5494481P112	Crystal freq = (OF -5.30 MHz) 9
----- DIODES AND RECTIFIERS -----		
CR1 thru CR4	19A115603P1	Silicon.
CR5		(Part of T2).

SYMBOL	GE PART NO.	DESCRIPTION
A2362		FIRST OSCILLATOR 19B216179G4
----- CAPACITORS -----		
C1 thru C6	5494481P112	Ceramic disc: 1000 pf ±10%, 1000 VDCW; sim to RMC Type JF Discap.
C30		(Part of T2).
C32 and C33		(Part of T2).
----- DIODES AND RECTIFIERS -----		
CR1 thru CR4	19A115250P1	Silicon, fast recovery, 225 mA, 50 PIV.
CR5		(Part of T2).
----- JACKS AND RECEPTACLES -----		
J1 thru J6	4033513P4	Contact, electrical; sim to Bead Chain L93-3.
----- INDUCTORS -----		
L1		(Part of T2).
L2 and L3	7488079P16	Choke, RF: 10 µh ±10%, 0.60 ohms DC res max; sim to Jeffers 4421-12K.
L4	7488079P*	Choke, RF: 2.20 µh ±10%, 1 ohm DC res max; sim to Jeffers 4411-12K.
----- TRANSISTORS -----		
Q1	19A115330P1	Silicon, NPN.
----- RESISTORS -----		
R1	3R152P272J	Composition: 2.7K ohms ±5%, 1/4 w.
R2	3R152P103J	Composition: 10K ohms ±5%, 1/4 w.
R3	3R152P102J	Composition: 1K ohms ±5%, 1/4 w.
R4	3R152P151J	Composition: 150 ohms ±5%, 1/4 w.
R5	3R152P101K	Composition: 100 ohms ±10%, 1/4 w.
R16		(Part of T2).
----- TRANSFORMERS -----		
T2		COIL ASSEMBLY 19B204421G2
----- CAPACITORS -----		
C30	5496218P250	Ceramic disc: 30 pf ±5%, 500 VDCW, temp coef -80 PPM.
C32	5496218P34	Ceramic disc: 3 pf ±0.25 pf, 500 VDCW, temp coef 0 PPM.
C33	5494481P12	Ceramic disc: 1000 pf ±10%, 1000 VDCW; sim to RMC Type JF Discap.
----- DIODES AND RECTIFIERS -----		
CR5	19A115250P1	Silicon, fast recovery, 225 mA, 50 PIV.
----- INDUCTORS -----		
L1	19A121093P1	Coil.
----- RESISTORS -----		
CR5	19A115250P1	Silicon, fast recovery, 225 mA, 50 PIV.
L1	19A121093P1	Coil.
----- RESISTORS -----		
R16	3R152P103K 19B209674P25	Composition: 10K ohms ±10%, 1/4 w. Tuning slug.
----- SOCKETS -----		
XY1 thru XY4		Socket assembly. Includes:
19B216043G1		
19D413071P1		Socket cavity.
19A115834P2		Electrical contact.

SYMBOL	GE PART NO.	DESCRIPTION	SYMBOL
		----- OSCILLATORS -----	
		NOTE: When reordering, specify ICOW Frequency. ICOW Frequency = (OF - 5.3 MHz) 9	
ru	4EG28A11	Integrated Circuit Oscillator Module (ICOW).	
	19D413070P1	Cap, decorative.	
5		HIGH IF AMPLIFIER 19B216109G1	
		----- CAPACITORS -----	
1	5494481P11	Ceramic disc: 1000 pf ±20%, 1000 VDCW; sim to RMC Type JF Discap.	
2	5493392P107	Ceramic, feed-thru: 1000 pf +100%-0%, 500 VDCW; sim to Allen Bradley Type FASC.	
3	5493392P108	Ceramic, stand-off: 22 pf ±10%, 500 VDCW; sim to Allen Bradley Type SS5D.	
4 thru 6		(Part of T1).	
7 nd 8 9	19A116080P105	Polyester: 0.047 µf ±10%, 50 VDCW.	
		(Part of T1).	
		----- TERMINALS -----	
1 thru 3	4029309P1	Feed-thru: 750 VRMS max, 5.5 amps; sim to Sealctro FT-SM-27.	
		----- INDUCTORS -----	
1		(Part of T1).	
2*	19A116632P1	Ferrite bead: sim to Pyroferic P5-1288. Added by REV B.	
		----- TRANSISTORS -----	
1*	19A115440P1	Silicon, NPN.	
		In REV C & earlier:	
	19A115666P1	Silicon, NPN.	
		----- RESISTORS -----	
1	3R152P511J	Composition: 510 ohms ±5%, 1/4 w.	
2	3R152P332K	Composition: 3.3K ohms ±10%, 1/4 w.	A2
3	3R152P682K	Composition: 6.8K ohms ±10%, 1/4 w.	
4	3R152P101K	Composition: 100 ohms ±10%, 1/4 w.	
5		(Part of T1).	
		----- TRANSFORMERS -----	
1		COIL ASSEMBLY 19B216109G1	
		----- CAPACITORS -----	
C4	5496218P265	Ceramic disc: 120 pf ±5%, 500 VDCW, temp coef -80 PPM.	
C5	5494481P111	Ceramic disc: 1000 pf ±20%, 1000 VDCW; sim to RMC Type JF Discap.	
C6	5494481P11	Ceramic disc: 1000 pf ±20%, 1000 VDCW; sim to RMC Type JF Discap.	
C9	5496218P246	Ceramic disc: 20 pf ±5%, 500 VDCW, temp coef -80 PPM.	
		----- RESISTORS -----	
R5	3R152P101K 19B209674P26	Composition: 100 ohms ±10%, 1/4 w. Tuning slug.	
2*		RF PRE-AMPLIFIER 19C317051G2 (When reordering A2372, be sure number on parts list agrees with that on the board assembly)	
		----- CAPACITORS -----	
2		(Part of T2).	
4		(Part of T4).	

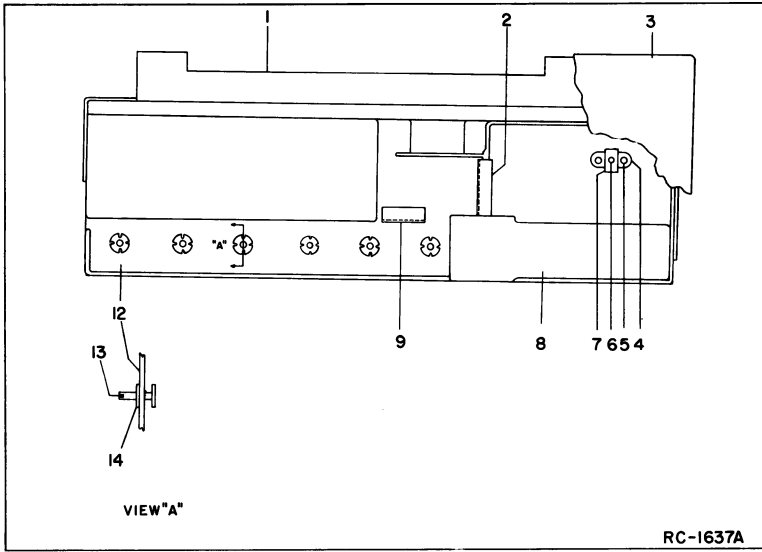


SCHEMATIC DIAGRAM

150.8—174 MHz, DUAL FRONT END
WITH ICOM OSCILLATOR

SYMBOL			GE PART NO.			DESCRIPTION		
P3						----- PLUGS ----- (Part of W3).		
Q1			19A116818P1			----- TRANSISTORS ----- N Channel, field effect: sim to Type 3N187.		
R1			3R152P103J			----- RESISTORS ----- Composition: 10K ohms $\pm 5\%$, 1/4 w.		
R2			3R152P472J			Composition: 4.7K ohms $\pm 5\%$, 1/4 w.		
R3 and R4			3R152P101J			Composition: 100 ohms $\pm 5\%$, 1/4 w.		
R5*			3R152P392J			Composition: 3.9K ohms $\pm 5\%$, 1/4 w. Earlier than REV A:		
			3R152P242J			Composition: 2.4K ohms $\pm 5\%$, 1/4 w.		
R6*			3R152P102J			Composition: 1K ohms $\pm 5\%$, 1/4 w. Added by REV B.		
W2			19A129857G1			----- CABLES ----- 3 inches long. Includes J2.		
W3			19A129856G1			5 inches long. Includes P3.		
						CHASSIS AND RF CIRCUIT 19D413462G1		
C2351 thru C2356			19B209135P1			----- CAPACITORS ----- (See mechanical parts, RC1637).		
C2360 thru C2363			5496267P10			Ceramic, feed-thru: 1000 pf $\pm 15\%$ -0%, 500 VDCW.		
C2364			19A115680P3			Tantalum: 22 μ f $\pm 20\%$, 15 VDCW; sim to Sprague Type 150D.		
C2365			5494481P12			Electrolytic: 20 μ f $\pm 15\%$ -10%, 2 VDCW; sim to Mallory Type TTX.		
C2367 and C2368						Ceramic disc: 1000 pf $\pm 10\%$, 1000 VDCW; sim to RMC Type JF Discap.		
J2351			19B205689G2			----- JACKS AND RECEPTACLES ----- Connector: 18 contacts.		
J2352			19A115465P1			Connector, coaxial; sim to Micon Electronics Type 1104.		
J2353 thru J2356			7147199P1			Connector: male contact; sim to Winchester Electronics 21803.		
J2357						(Part of W2351).		
J2358 thru J2361						(Part of W2353).		
L2352			19B216112G3			----- INDUCTORS ----- Coil.		
L2354			19B216112G7			Coil.		
L2356			19B216112G7			Coil.		
L2358			19B216112G7			Coil.		
L2360			19B216112G5			Coil.		
L2362			19B216112G1			Coil.		
L2363 and L2364			7488079P16			Choke, RF: 10 μ h $\pm 10\%$, 0.6 ohm DC res max; sim to Jeffers 4421-7K.		
P2351 thru P2353			4029840P2			----- PLUGS ----- Contact, electrical; sim to Amp 42827-2.		
P2362 thru P2365						(Part of W2353).		
R2351*			3R152P331K			----- RESISTORS ----- Composition: 330 ohms $\pm 10\%$, 1/4 w. Deleted by REV A.		
R2352			19A116278P444			Metal film: 0.28 megohm $\pm 2\%$, 1/2 w.		

SYMBOL			GE PART NO.			DESCRIPTION		
TB1			7487424P7			----- TERMINAL BOARDS ----- Miniature, phen: 4 terminals.		
W2351			19B205634G1			----- CABLES ----- Coaxial cable: approx 34 inches long.		
J2357			19B209122P3			----- JACKS AND RECEPTACLES ----- Receptacle: coaxial; sim to Vendor Piece A-183.		
W2353			19B219304G1			RF Cable: approx 15-1/4 inches long.		
J2358 thru J2361			4029840P2			----- JACKS AND RECEPTACLES ----- Contact, electrical: sim to Amp 42827-2.		
P2362 thru P2365			7147199P1			----- PLUGS ----- Connector: male contact; sim to Winchester Electronics 21803.		
19A115700P2						----- MISCELLANEOUS ----- Core, torridal.		
						HARNES ASSEMBLY 19D413462G2 (Includes C2367, C2368, J2351, P2351, R2352, W2353)		
19C317281G1						RECEIVER MODIFICATION KIT 19A127692G1		
19B204924G1						Power separator.		
19A127259G1						Cable. (Connects to P443).		
19A115539P1						Cable. (Connects to F11).		
4037914P2						Tap screw. (Mounts dual front end to frame).		
3R152P123K						Channel pad.		
C1			5493392P107			Resistor, Composition: 12K ohms $\pm 10\%$, 1/4 w. (Hooks to input and ground on F11).		
CR1 thru CR3			19A115250P1			DIODE KIT 19B219305G1		
1			19C303649P1			----- CAPACITORS ----- Ceramic, stand-off: 1000 pf $\pm 10\%$ -0%, 500 VDCW; sim to Allen-Bradley Type SS5D.		
2			19A121222P1			----- DIODES AND RECTIFIERS ----- Silicon, fast recovery, 225 mA, 50 PIV.		
3			19C303648G1			MECHANICAL PARTS (SEE RC1637)		
4			4039307P1			Support. (Mounts cover).		
5			19A115793P1			Angle support. (Used with C2362 & C2363).		
6			19B200525P9			Cover.		
7			4033089P1			Crystal socket. (Part of XY1).		
8			19B216072P1			Electrical contact; sim to Methode 752V (PB). (Part of XY1).		
9			19A121221P1			Rivet. (Part of XY1).		
10			19B216070P1			Clip. (Part of XY1).		
11						Plate.		
12			19C311659G1			Angle support. (Used with C2360 & C2361).		
13			4036765G4			RF plate. (Access to RF circuit).		
14			7137968P8			(Not Used).		
15						RF Chassis.		
						Screw; 6-32. (Part of C2351-C2356).		
						Nut, stamped: thd size No. 6-32; sim to Palnut T0632005. (Part of C2351-C2356).		
						(Not Used).		



PRODUCTION CHANGES

Changes in the equipment to improve performance or to simplify circuits are identified by a "Revision Letter", which is stamped after the model number of the unit. The revision stamped on the unit includes all previous revisions. Refer to the Parts List for descriptions of parts affected by these revisions.

REV. A - RF Preamp A2372 19C317051G2

To provide band-end tuning at 150.8 MHz. Changed C2 in transformer T2.

REV. A - Chassis and RF Circuit 19D413462G1

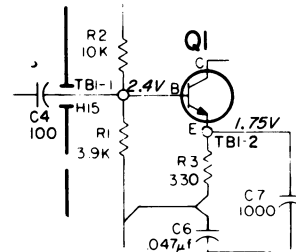
Incorporated into initial shipment

REV. B - To prevent oscillation in Hi IF Amplifier.
Added L2.

REV. C - To prevent oscillation and increase injection from multipliers.

On 2nd Mult Board A2354, 19B216107G2
Deleted R1 and R2. Changed Q1 and R
Added L4

Schematic Diagram was:

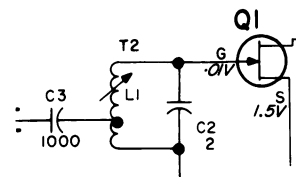


On 1st Mixer Board A2352, 19B216077G2
Added R6.

REV. D - Chassis and RF Circuit 19D413462G1

To improve design. Changed A2354

Schematic was:



REV. E - Incorporate new transistor. Changed
Q1 on First Mixer.

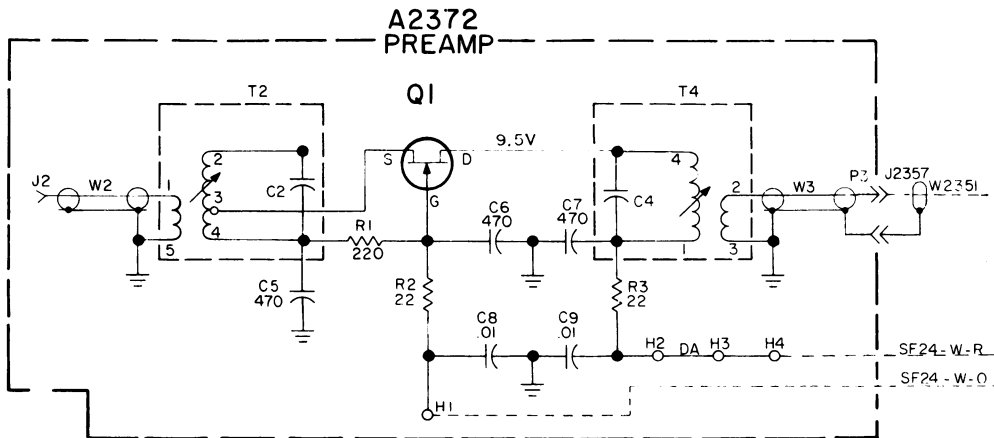
REV. A - Modification Kit 19A127479G1

	1	2	3	4	5	6	7
1	1						
2		1					
3			1				
4				1			
5					1		
6						1	
7							1

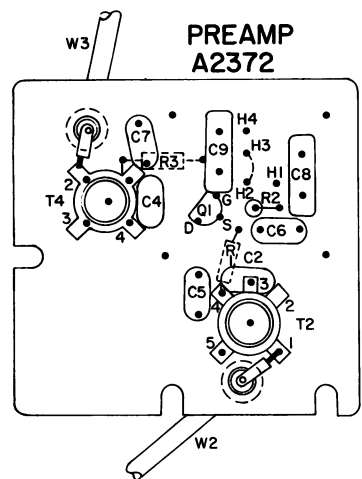
Changed Pre-Amp Board Assembly from 19C317051G2 to 19B226039G1.

REV. B - To improve reliability. Added R6.

Schematic Diagram was:



Outline Diagram Was:



Alignment Procedure Was:

6.	B (2nd If Amp on Receiver)	Pin 2	C2351 thru C2356	See Procedure	Apply an on-frequency signal to the DFE antenna jack. On DFE's with Pre-amp, tune T2 and T4 for maximum meter reading. On all DFE's tune C2351 thru C2356 for maximum meter reading, keeping signal below saturation. Then return C2351 thru C2356 slightly for maximum quieting.
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